

HIGH-PERFORMANCE, LOW-CURRENT SIGFOX™ GATEWAY

Features

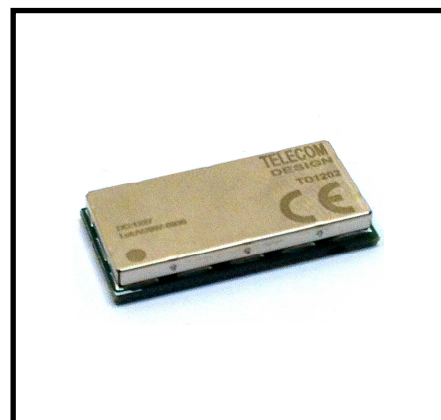
- SIGFOX READY™
- Frequency range = ISM 868 MHz
- Receive sensitivity = -126 dBm
- Modulation
 - (G)FSK, 4(G)FSK, GMSK
 - OOK
- Max output power
 - +14 dBm
- Low active radio power consumption
 - 13/16 mA RX
 - 37 mA TX @ +10 dBm
- Power supply = 2.3 to 3.3 V
- LGA25 (25.4x12.7x3.81mm) Land Grid Array package
- Available in several conditioning methods

Applications

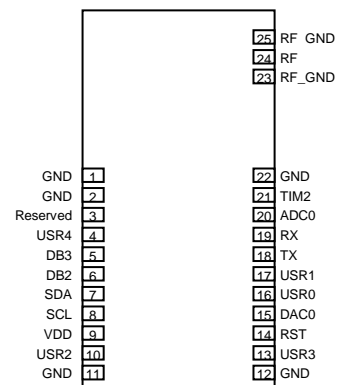
- SIGFOX™ transceiver (fully certified)
- Sensor network
- Health monitors
- Remote control
- Home security and alarm
- Telemetry
- Industrial control

Description

Telecom Design's TD1207 devices are high performance, low current SIGFOX™ gateways. The combination of a powerful radio transceiver and a state-of-the-art ARM Cortex M3 baseband processor achieves extremely high performance while maintaining ultra-low active and standby current consumption. The TD1207 device offers an outstanding RF sensitivity of –126 dBm while providing an exceptional output power of up to +14 dBm with unmatched TX efficiency. The TD1207 device versatility provides the gateway function from a local Narrow Band ISM network to the long-distance Ultra Narrow Band SIGFOX™ network at no additional cost. The broad range of analog and digital interfaces available in the TD1207 module allows any application to interconnect easily to the SIGFOX™ network. The LVTTTL low-energy UART, along with the numerous GPIOs can control any kind of external sensors or activators. Featuring an AES encryption engine and a DMA controller, the powerful 32-bit ARM Cortex-M3 baseband processor can implement highly complex and secure protocols in an efficient environmental and very low consumption way.



Pin Assignments



Patents pending

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Functional Block Diagram

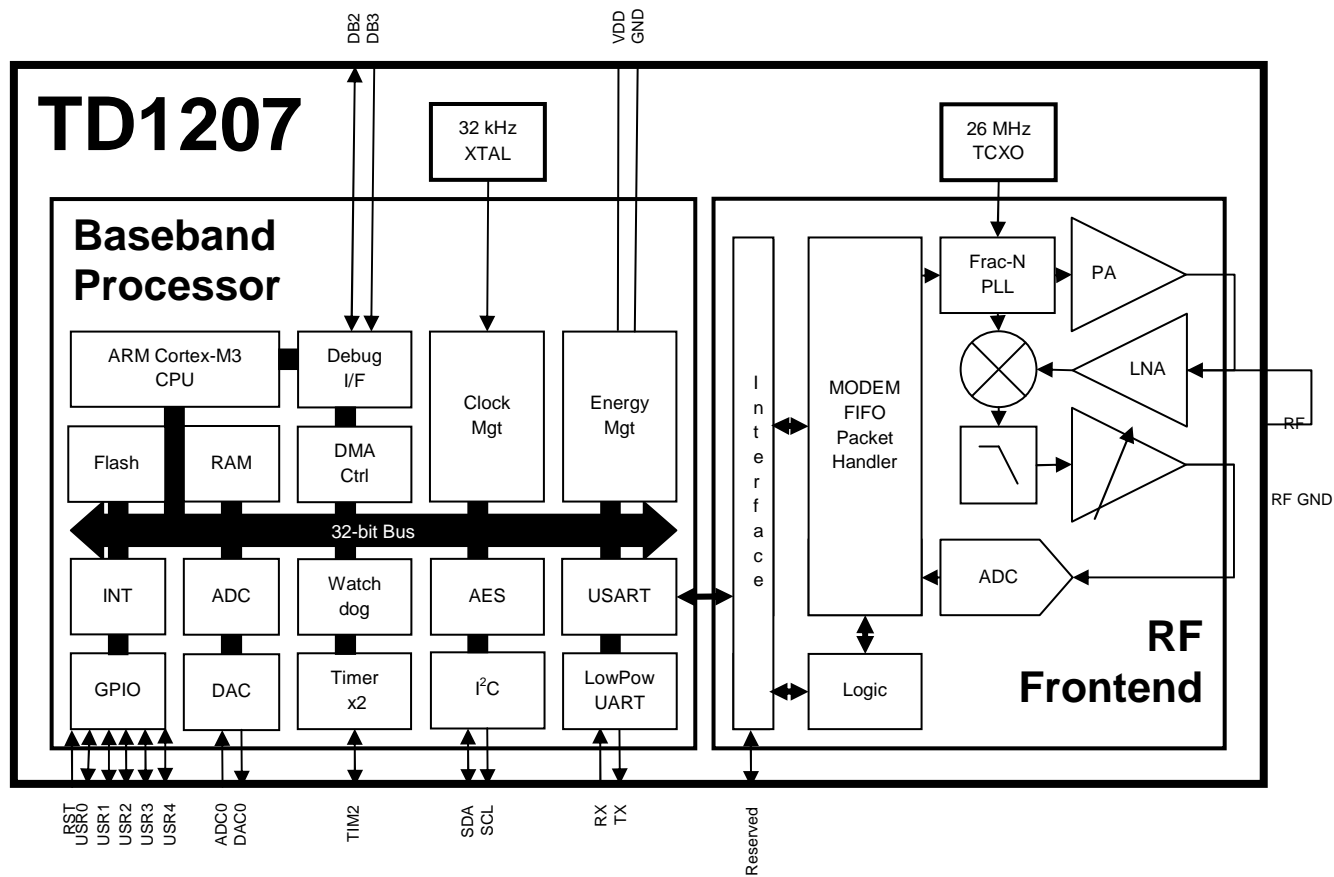


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1 Electrical Specifications

Table 1. Absolute Maximum Ratings

Parameter	Value	Units
V_{DD} to GND	0 to +3.3	V
Instantaneous $V_{RF-peak}$ to GND on RF Pin	-0.3 to +8.0	V
Sustained $V_{RF-peak}$ to GND on RF Pin	-0.3 to +6.5	V
Voltage on Digital Inputs	0 to V_{DD}	V
Voltage on Analog Inputs	0 to V_{DD}	V
RX Input Power	+10	dBm
Operating Ambient Temperature Range T_A	-30 to +75	°C
Storage Temperature Range T_{STG}	-40 to +125	°C
Maximum soldering Temperature	260	°C
Note: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at or beyond these ratings in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Power Amplifier may be damaged if switched on without proper load or termination connected. TX matching network design will influence TX $V_{RF-peak}$ on RF pin. Caution: ESD sensitive device.		

Table 2- DC Power Supply Characteristics¹

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Voltage Range ²	V _{DD}		2.3	3.0	3.3	V
Power Saving Mode ²	I _{Sleep}	Sleep current using the 32 kHz crystal @ 25°C	1.5	1.8	3.5	µA
Active CPU Mode	I _{Active}	CPU performing active loop @ 14 MHz	2.55	3.0	3.45	mA
Active CPU Mode + RX Mode Current ²	I _{RX}		—	13	16	mA
Active CPU Mode + TX Mode Current ²	I _{TX +14}	+14 dBm output power, 868 MHz, 3.3 V	—	49	—	mA
	I _{TX +10}	+10 dBm output power, 868 MHz, 3.3 V	—	37	—	mA

Notes:

1. All specifications guaranteed by production test unless otherwise noted. Production test conditions and max limits are listed in the “Production Test Conditions” section in “1.1. Definition of Test Conditions” on page 5.
2. Guaranteed by qualification. Qualification test conditions are listed in the “Qualification Test Conditions” section in “1.1. Definition of Test Conditions” on page 14.

Table 3. Transmitter RF Characteristics¹

Parameter	Symbol	Conditions	Min	Typ	Max	Units
TX Frequency Range ²	F _{TX}		868.0	—	869.7	MHz
Modulation Deviation Range ³	Δf	868.0-869.7 MHz	—	1.5	—	MHz
Modulation Deviation Resolution ³	F _{RES}	868.0-869.7 MHz	—	28.6	—	Hz
Frequency Error ²	F _{ERR_25}	868.0-869.7 MHz, 25°C, 3.3 V	—	±2	—	kHz
	F _{ERR_M20}	868.0-869.7 MHz, -20°C, 3.3 V	—	±3	—	kHz
	F _{ERR_55}	868.0-869.7 MHz, 55°C, 3.3 V	—	±3	—	kHz
Average Conducted Power ²	P _{AVCDP1}	-20°C to 55°C, 868.0 MHz to 868.6 MHz, 3.3 V	—	—	14	dBm
	P _{AVCDP2}	-20°C to 55°C, 868.6 MHz to 868.7 MHz, 3.3 V	—	—	10	dBm
	P _{AVCDP3}	-20°C to 55°C, 868.7 MHz to 869.2 MHz, 3.3 V	—	—	14	dBm
	P _{AVCDP4}	-20°C to 55°C, 869.2 MHz to 869.25 MHz, 3.3 V	—	—	10	dBm
	P _{AVCDP5}	-20°C to 55°C, 869.25 MHz to 869.3 MHz, 3.3 V	—	—	10	dBm
	P _{AVCDP6}	-20°C to 55°C, 869.3 MHz to 869.4 MHz, 3.3 V	—	—	10	dBm
	P _{AVCDP7}	-20°C to 55°C, 869.65 MHz to 869.7 MHz, 3.3 V	—	—	14	dBm
Transient Power ²	P _{TP}	868.0-869.7 MHz, 25°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	—	3	dB
Adjacent Channel Power ²	P _{ACP_25}	868.0-869.7 MHz, 25°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-50	—	dBm
	P _{ACP_M20}	868.0-869.7 MHz, -20°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-51	—	dBm
	P _{ACP_55}	868.0-869.7 MHz, 55°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-50	—	dBm
Spurious Emissions ²	P _{OB_TX1}	Frequencies < 30 MHz, 868.0-869.7 MHz, 25°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-82	—	dBm
	P _{OB_TX2}	Frequencies < 1 GHz, 868.0-869.7 MHz, 25°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-58	—	dBm
	P _{OB_TX3}	Frequencies > 1 GHz, 868.0-869.7 MHz, 25°C, 3.3 V, 4800 bps, deviation 2500 Hz, cable loss 0.2 dB, antenna gain 2 dBi	—	-37	—	dBm

Notes:

- All specifications guaranteed by production test unless otherwise noted. Production test conditions and max limits are listed in the “Production Test Conditions” section of “1.1. Definition of Test Conditions” on page 5.
- Guaranteed by qualification. Qualification test conditions are listed in the “Qualification Test Conditions” section in “1.1. Definition of Test Conditions” on page 14.
- Guaranteed by component specification.

Table 4. Receiver RF Characteristics¹

Parameter	Symbol	Conditions	Min	Typ	Max	Units
RX Frequency Range ²	F _{RX}		868.0	—	869.7	MHz
Synthesizer Frequency Resolution ³	F _{RES}	868.0-869.7 MHz	—	28.6	—	Hz
Blocking ^{2,4}	2M _{BLOCK}	Frequency offset ± 2 MHz, 868.0-869.7 MHz, 25°C, 3.3 V	—	-38	—	dB
	10M _{BLOCK}	Frequency offset ± 10 MHz, 868.0-869.7 MHz, 25°C, 3.3 V	—	-62	—	dB
Spurious Emissions ²	P _{OB_RX1}	From 9 kHz to 1 GHz, 868.0-869.7 MHz, 25°C, 3.3 V	—	-84	—	dBm
	P _{OB_RX2}	From 1 GHz to 6 GHz, 868.0-869.7 MHz, 25°C, 3.3 V	—	-70	—	dBm
RX Sensitivity ³	P _{RX_0.5}	(BER < 0.1%) (500 bps, GFSK, BT = 0.5, $\Delta f = \pm 250$ Hz)	—	-126	—	dBm
	P _{RX_40}	(BER < 0.1%) (40 kbps, GFSK, BT = 0.5, $\Delta f = \pm 20$ kHz)	—	-110	—	dBm
	P _{RX_100}	(BER < 0.1%) (100 kbps, GFSK, BT = 0.5, $\Delta f = \pm 50$ kHz)	—	-106	—	dBm
	P _{RX_125}	(BER < 0.1%) (125 kbps, GFSK, BT = 0.5, $\Delta f = \pm 62.5$ kHz)	—	-105	—	dBm
	P _{RX_500}	(BER < 0.1%) (500 kbps, GFSK, BT = 0.5, $\Delta f = \pm 250$ kHz)	—	-97	—	dBm
	P _{RX_9.6}	(BER < 0.1%) (9.6 kbps, GFSK, BT = 0.5, $\Delta f = \pm 2.4$ kHz)	—	-110	—	dBm
	P _{RX_1M}	(BER < 0.1%) (1 Mbps, GFSK, BT = 0.5, $\Delta f = \pm 1.25$ kHz)	—	-88	—	dBm
	P _{RX_OOK}	(BER < 0.1%, 4.8 kbps, 350 kHz BW, OOK, PN15 data)	—	-109	—	dBm
		(BER < 0.1%, 40 kbps, 350 kHz BW, OOK, PN15 data)	—	-104	—	dB
		(BER < 0.1%, 120 kbps, 350 kHz BW, OOK, PN15 data)	—	-99	—	dBm
RSSI Resolution ³	RES _{RSSI}		—	± 0.5	—	dB

Notes:

1. All specifications guaranteed by production test unless otherwise noted. Production test conditions and max limits are listed in the "Production Test Conditions" section of "1.1. Definition of Test Conditions" on page 5.
2. Guaranteed by qualification. Qualification test conditions are listed in the "Qualification Test Conditions" section in "1.1. Definition of Test Conditions" on page 14.
3. Guaranteed by component specification.
4. The typical blocking values were obtained while seeking for EN 300-220 Category 2 compliance only. The typical value specified in the component datasheet are -75 dB and -84 dB at 1 and 8 MHz respectively, with desired reference signal 3 dB above sensitivity, BER = 0.1%, interferer is CW, and desired is modulated with 2.4 kbps, $\Delta F = 1.2$ kHz GFSK with BT = 0.5, RX channel BW = 4.8 kHz. The RF component manufacturer provides a reference design featuring a SAW filter which is EN 300-220 Category 1 compliant. Please contact Telecom Design for more information on EN 300-220 Category 1 compliance.

Table 5. All Digital I/O (except DB1) DC & AC Characteristics¹

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Input Low Voltage ²	V_{IOIL}		—	—	$0.3V_{DD}$	V
Input High Voltage ²	V_{IOIH}		$0.7V_{DD}$	—	—	V
Output High Voltage ²	V_{IOOH}	Sourcing 6 mA, $V_{DD} = 3.0V$, Standard Drive Strength	$0.95V_{DD}$	—	—	V
		Sourcing 20 mA, $V_{DD} = 3.0V$, High Drive Strength	$0.9V_{DD}$	—	—	V
Output Low Voltage ²	V_{IOOL}	Sinking 6 mA, $V_{DD}=3.0V$, Standard Drive Strength	—	—	$0.05V_{DD}$	V
		Sinking 20 mA, $V_{DD}=3.0V$, High Drive Strength	—	—	$0.1V_{DD}$	V
Input Leakage Current ²	I_{IOLEAK}	High Impedance I/O connected to GND or V_{DD}	—	—	± 25	nA
I/O Pin Pull-Up Resistor ²	R_{PU}		—	40	—	k Ω
I/O Pin Pull-Down Resistor ²	R_{PD}		—	40	—	k Ω
Internal ESD Series Resistor ²	R_{IOESD}		—	200	—	Ω
Pulse Width of Pulses to be Removed by the Glitch Suppression Filter ²	$t_{IOGLITCH}$		10	—	50	ns
Output Fall Time ²	t_{IOOF}	0.5 mA Drive Strength and Load Capacitance $C_L = 12.5$ to 25 pF	$20+0.1C_L$	—	250	ns
		2 mA Drive Strength and Load Capacitance $C_L = 350$ to 600 pF	$20+0.1C_L$	—	250	ns
I/O Pin Hysteresis ($V_{IOTHR+} - V_{IOTHR-}$) ²	V_{IOHYST}	$V_{DD} = 2.3$ to 3.3 V	$0.1V_{DD}$	—	—	V

Notes:

1. All specifications guaranteed by production test unless otherwise noted. Production test conditions and max limits are listed in the "Production Test Conditions" section of "1.1. Definition of Test Conditions" on page 14.
2. Guaranteed by component specification.

Table 6. DB1 Digital I/O DC & AC Characteristics¹

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Input Low Voltage ²	V_{DB1IL}		—	—	$0.3V_{DD}$	V
Input High Voltage ²	V_{DB1IH}		$0.7V_{DD}$	—	—	V
Output High Voltage ²	V_{DB1OH}	Sourcing 7.4 mA, $V_{DD} = 3.3V$, Drive Strength = HL	$0.8V_{DD}$	—	—	V
Output Low Voltage ²	V_{DB1OL}	Sinking 8.5 mA, $V_{DD} = 3.3V$, Drive Strength = HL	—	—	$0.2V_{DD}$	V
Input Leakage Current ²	$I_{DB1LEAK}$	High Impedance I/O connected to GND or V_{DD}	—	—	± 10	μA
Input Capacitance ²	C_{DB1IN}		—	2	—	pF
Output Rise Time ²	t_{DB1OR}	$0.1V_{DD}$ to $0.9V_{DD}$, $C_L = 10$ pF, Drive Strength = HH	—	2.3	—	ns
Output Fall Time ²	t_{DB1OF}	$0.9V_{DD}$ to $0.1V_{DD}$, $C_L = 10$ pF, Drive Strength = HH	—	2	—	ns
Notes:						
1. All specifications guaranteed by production test unless otherwise noted. Production test conditions and max limits are listed in the “Production Test Conditions” section of “1.1. Definition of Test Conditions” on page 14.						
2. Guaranteed by component specification.						

1.1 Definition of Test Conditions

1.1.1 Production Test Conditions:

- $T_A = +25^{\circ}\text{C}$
- $V_{DD} = +3.3\text{ VDC}$
- Production test schematics (unless noted otherwise)
- All RF input and output levels referred to the pins of the TD1207 module

1.1.2 Qualification Test Conditions:

- $T_A = -30$ to $+75^{\circ}\text{C}$ (Typical $T_A = 25^{\circ}\text{C}$)
- $V_{DD} = +2.3$ to 3.3 VDC (Typical $V_{DD} = 3.0\text{ VDC}$)
- Using TX/RX Split Antenna reference design or production test schematic
- All RF input and output levels referred to the pins of the TD1207 module

2 Functional Description

The TD1207 devices are high-performance, low-current, wireless SIGFOX™ gateways. The wide operating voltage range of 2.3–3.3 V and low current consumption make the TD1207 an ideal solution for battery powered applications. The TD1207 operates as a time division duplexing (TDD) transceiver where the device alternately transmits and receives data packets. The device uses a single-conversion mixer to downconvert the 2-level FSK/GFSK or OOK/ASK modulated receive signal to a low IF frequency. Following a programmable gain amplifier (PGA) the signal is converted to the digital domain by a high performance $\Delta\Sigma$ ADC allowing filtering, demodulation, slicing, and packet handling to be performed in the built-in DSP increasing the receiver's performance and flexibility versus analog based architectures. The demodulated signal is output to the baseband CPU by reading the 64-byte RX FIFO.

A single high precision local oscillator (LO) is used for both transmit and receive modes since the transmitter and receiver do not operate at the same time. The LO is generated by an integrated VCO and $\Delta\Sigma$ Fractional-N PLL synthesizer. The synthesizer is designed to support configurable data rates from 0.123 kbps to 1 Mbps. The TD1207 operates in the frequency bands of 868.0–869.7 MHz with a maximum frequency accuracy step size of 28.6 Hz. The transmit FSK data is modulated directly into the $\Delta\Sigma$ data stream and can be shaped by a Gaussian low-pass filter to reduce unwanted spectral content.

The power amplifier (PA) supports output power up to +14 dBm with very high efficiency, consuming only 37 mA at +10 dBm. The integrated power amplifier can also be used to compensate for the reduced performance of a lower cost, lower performance antenna or antenna with size constraints due to a small form-factor. The PA is single-ended to allow for easy antenna matching and low BOM cost. The PA incorporates automatic ramp-up and ramp-down control to reduce unwanted spectral spreading. A highly configurable packet handler allows for autonomous encoding/decoding of nearly any packet structure.

As both the local Narrow Band ISM network and the long-distance Ultra Narrow Band SIGFOX™ network can be addressed seamlessly, the TD1207 device provides a natural gateway function at no additional cost. Thus, the same TD1207 module can be used both for local RF communication with peer modules, and also connect to the wide-area SIGFOX™ RF network.

The broad range of analog and digital interfaces available in the TD1207 module allows any application to interconnect easily to the SIGFOX™ network. The LVTTL low-energy UART, along with the numerous GPIOs can control any kind of external sensors or activators. Featuring an AES encryption engine and a DMA controller, the powerful 32-bit ARM Cortex-M3 baseband processor can implement highly complex and secure protocols in an efficient environmental and very low consumption way. This unique combination of a powerful 32-bit ARM Cortex-M3 CPU including innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of intelligent peripherals allows any application to connect to the SIGFOX™ network.

The application shown in Figure 1 shows the minimum interconnection required to operate the TD1207 module.

Basically, only the 5 GND, 2 RF_GND, V_{DD} , TX, RX and RF antenna pin connections are necessary. The RST (reset) pin connection is not mandatory and this pin can be left floating if not used.

A 10 μ F/6.3V decoupling capacitor must be added as close as possible to the V_{DD} pin.

The TX/RX pins are LVTTL-compatible and feature internal pull-up resistors.

A 50 Ω matched RF antenna must be connected to the RF pin, with a low-capacitance (< 0.5 pF) TVS diode to protect the RF input from ESD transients.

The connection of a super-blue LED with series current-limiting resistor of 220 Ω on pin TIM2 is recommended in order to display the bootloader status at boot time.

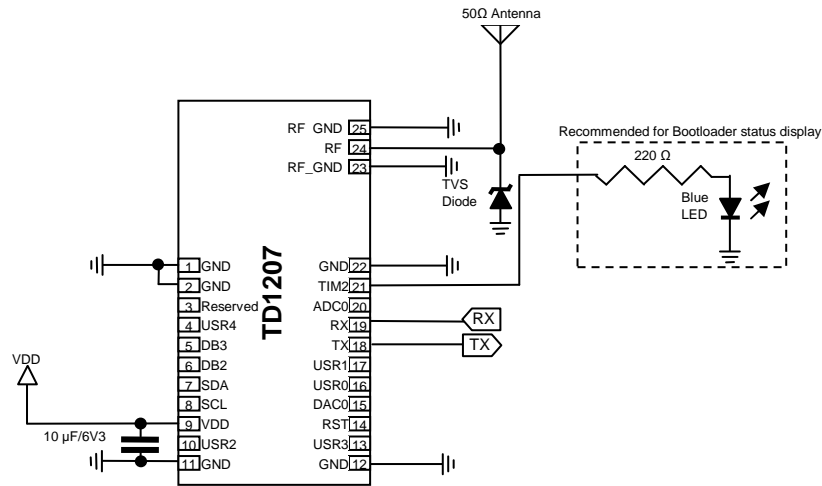


Figure 1. Typical Application

Note: The TVS diode used for protecting the RF input against ESD must be of low-capacitance (0.5 pF typical) type, e.g. ESD9R3.3ST5G (On Semiconductor), for example.

3 Module Interface

3.1 Low-Power UART (Universal Asynchronous Receiver/Transmitter)

The TD1207 communicates with the host MCU over a standard asynchronous serial interface consisting of only 2 pins: TX and RX. The TX pin is used to send data from the TD1207 module to the host MCU, and the RX pin is used to receive data into the TD1207 module coming from the host MCU.

This interface allows two-way UART communication to be performed in low energy modes, using only a few μA during active communication and only 150 nA when waiting for incoming data.

This serial interface is designed to operate using the following serial protocol parameters:

- LVTTTL electrical level
- 9600 bps
- 8 data bits
- 1 stop bit
- No parity
- No hardware/software flow control

This interface operates using LVTTTL signal levels to satisfy the common interface to a low power host MCU. If an EIA RS232-compliant interface voltage level is required, an RS232 level translator circuit must be used. It is also possible to use a common USB/UART interface chip to connect to an USB bus.

Over this serial interface, the TD1207 device provides a standard Hayes “AT” command set used to control the module using ASCII readable commands and get answers, as well as to send or receive data.

The list of available commands with their corresponding arguments and return values, a description of their operation and some examples are detailed into the “*TD1207 Reference Manual*”.

3.2 GPIO (General Purpose Input/Output)

Apart from the TX and RX UART pins, and the RF pins, all signal pins are available as general-purpose inputs/outputs. This includes of course the generic USR0, USR1, USR2, USR3 and USR4 pins, but also the ADC0, TIM2, DAC0, SCL, SDA, DB2, DB3 pins when not used for their main function. This configuration can be performed using “AT” commands, please refer to the “*TD1207 Reference Manual*” for details.

All the USR0, USR1, USR2, USR3, USR4, ADC0, TIM2, DAC0, SCL, SDA, DB2, DB3 pins can be configured individually as tristate (default reset state), push-pull, open-drain, with/without pull-up or pull-down resistor, and with a programmable drive strength (0.5 mA/2 mA/6 mA/20 mA).

When configured as inputs, these pins feature an optional glitch suppression filter and full (rising, falling or both edges) interrupt with wake-up from low-power mode capabilities. Of course, the pin configuration is retained even when using these low-power modes.

The operation of the GPIOs is controlled by the mean of Hayes “AT” commands sent over the UART interface. To obtain a list of the available commands with their corresponding arguments and return values, a description of their operation and some examples, please refer to the “*TD1207 Reference Manual*”.

3.3 RST (Reset)

The TD1207 module features an active-low RST pin. This pin is held high by an internal pull-up resistor, so when not used, this pin can be left floating.

3.4 RF Antenna

The TD102 support a single-ended RF pin with 50 Ω characteristic impedance for connecting a matched-impedance external antenna. This pin is physically surrounded by 2 RF GND pins for better noise immunity.

3.5 VDD & GND

The TD1207 provides 5 GND pins and 2 RF_GND pins: all of them must be connected to a good ground plane.

A 10 μ F/6.3 V decoupling capacitor should be placed as closed as possible to the single VDD pin.

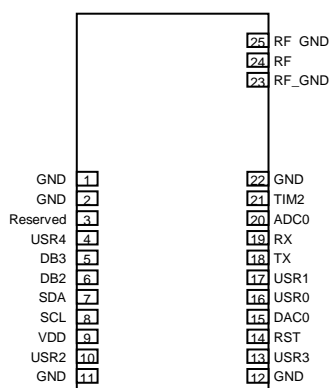
4 Bootloader

The TD1207 module contains an integrated bootloader which allows reflashing the module firmware either over the RX/TX UART connection, or over the air using the built-in RF transceiver.

The bootloader is automatically activated upon module reset. Once activated, the bootloader will monitor the UART/RF activity for a 200 ms period, and detect an incoming update condition.

If the update condition is met, the TD1207 will automatically proceed to flash the new firmware with safe retry mechanisms, or falls back to normal operation.

5 Pin Descriptions



Pin	Pin Name	I/O	Description
1	GND	GND	Connect to PCB ground
2	GND	GND	Connect to PCB ground
3	Reserved	I/O	Reserved pin – Do not connect
4	USR4	I/O	General Purpose Low-Power Digital I/O
5	DB3	I	SWDCLK (SWD Clock) Signal This signal provides the SWD clock signal to the integrated TD1207 ARM® CPU.
6	DB2	I/O	SWDIO (SWD Data I/O) Signal This signal provides the SWD programming/debugging signal interface to the integrated TD1207 ARM® CPU.
7	SDA	I/O	General Purpose Low-Power Digital I/O
8	SCL	I/O	General Purpose Low-Power Digital I/O
9	VDD	VDD	+2.3 to +3.3 V Supply Voltage Input The recommended VDD supply voltage is +3.0V. Connect a 10 µF capacitor as close as possible to this input.
10	USR2	I/O	General Purpose Low-Power Digital I/O
11	GND	GND	Connect to PCB ground
12	GND	GND	Connect to PCB ground
13	USR3	I/O	General Purpose Low-Power Digital I/O
14	RST	I	Active Low RESET input signal This signal resets the TD1207 module to its initial state. If not used, this signal can be left floating, as it is internally pulled up by an integrated resistor.
15	DAC0	I/O	General Purpose Low-Power Digital I/O
16	USR0	I/O	General Purpose Low-Power Digital I/O
17	USR1	I/O	General Purpose Low-Power Digital I/O
18	TX	O	Low-Power UART Data Transmit Signal This signal provides the UART data going from the TD1207 module out to the host application processor. This signal is internally pulled up by an integrated resistor.

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19	RX	I	Low-Power UART Data Receive Signal This signal provides the UART data coming from the host application processor going to the TD1207 module. This signal is internally pulled up by an integrated resistor.
20	ADC0	I/O	General Purpose Low-Power Digital I/O
21	TIM2	I/O	General Purpose Low-Power Digital I/O
22	GND	GND	Connect to PCB ground
23	RF_GND	GND	Connect to PCB ground
24	RF	RF	50 Ω Antenna Connection
25	RF_GND	GND	Connect to PCB ground

6 Ordering Information

Part Number	Description	Package Type	Operating Temperature
TD1207	ISM SIGFOX™ gateway	LGA25 Pb-free	-30° to +75°C

The TD1207 ISM SIGFOX™ gateway module is available in several conditionings.

Please contact Telecom Design for more information.

7 Package Outline

Figure 2 illustrates the package details for the TD1207.

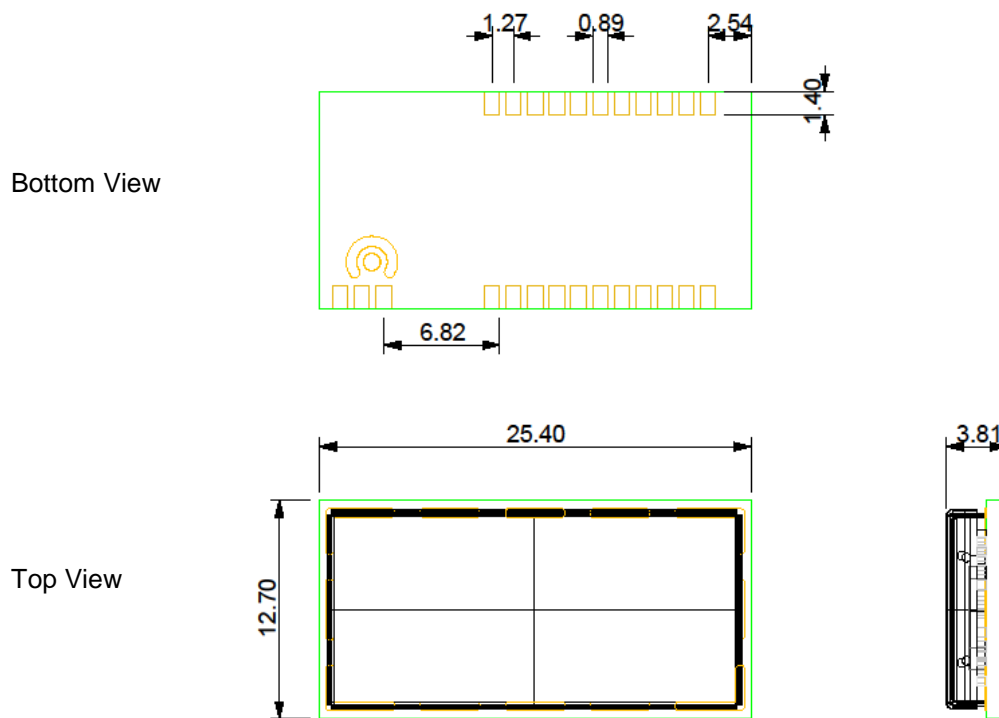


Figure 2. 25-Pin Land Grid Array (LGA)

Notes:

1. All dimensions are shown in millimeters (mm) unless otherwise noted.

8 PCB Land Pattern

Figure 3 illustrates the PB land pattern details for the TD1207.

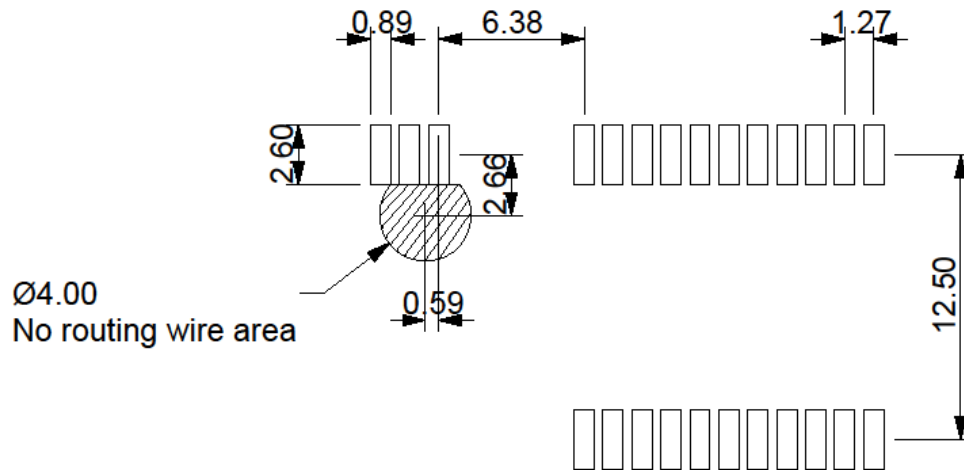


Figure 3. PCB Land Pattern

Notes:

1. All dimensions are shown in millimeters (mm) unless otherwise noted.

9 Soldering Information

9.1 Solder Stencil

The TD1207 module is designed for RoHS reflow process surface mounting.

For proper module assembly, the solder paste must be applied on the receiving PCB using a metallic stencil with a recommended 0.150 µm thickness.

9.2 Reflow soldering profile

The recommendation for lead-free solder reflow from IPC/JEDEC J-STD-020D Standard should be followed.

Below are typical reflow soldering profiles for a medium-size board:

Setpoints	1	2	3	4	5	6	7	8	9
Top (°C)	145	155	165	175	185	195	230	250	250
Bottom (°C)	145	155	165	175	185	195	230	250	250
Notes: Conveyor Speed is 65.00 cm / min									

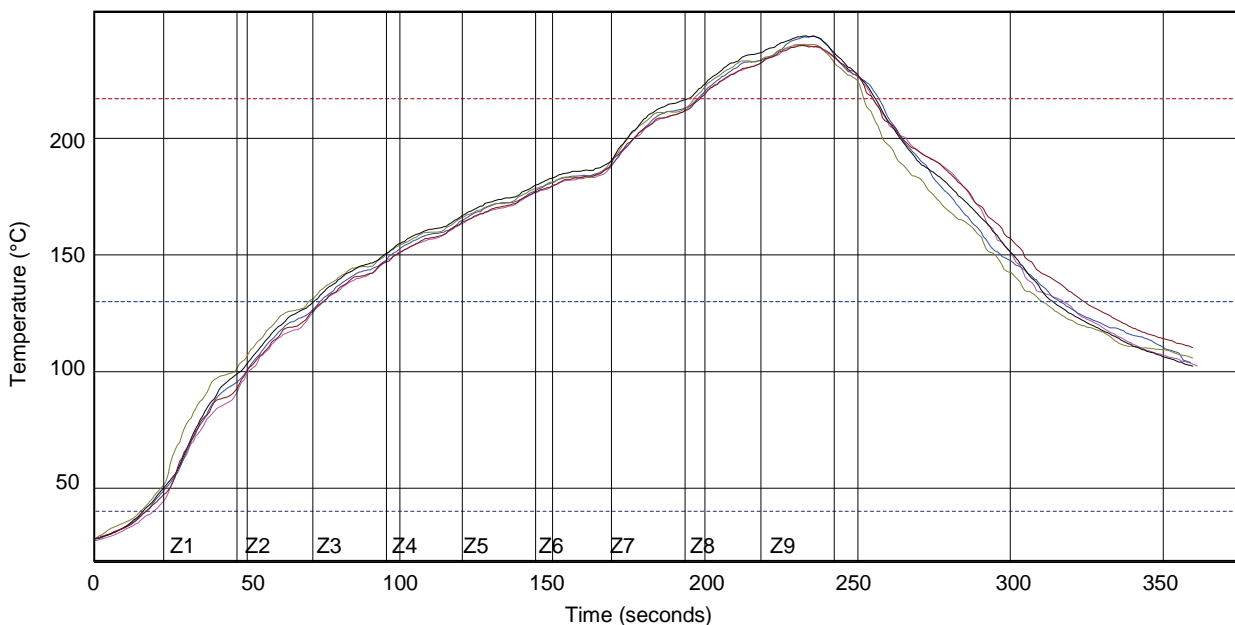


Figure 4 - Reflow Soldering Profile

Run	Preheat (s) 40-130°C	Soak Time (s) 130-217°C	Reflow Time (s) / 217°C	Peak Temp (°C)	Max. Slope1 (°C / s) (40-130°C)	Max. Slope2 (°C / s) (250-150°C)
2	56.04	122.40	58.66	239.00	1.53	-2.78
3	56.93	123.72	59.45	243.93	1.56	-2.79
4	55.34	124.25	57.34	239.45	1.54	-2.87
5	55.92	122.53	61.46	244.00	1.57	-2.77
6	58.12	123.38	57.89	239.84	1.53	-2.73

For more information on reflow soldering process profiling, please visit the <http://kicthermal.com/> website.

DOCUMENT CHANGE LIST

Revision 1.0

- First Release

Revision 1.1

- pages 17-18-19, pin description table was duplicated

NOTES:

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